

Di Yang

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

154
citations

1163117
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1588992
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10
docs citations

10
times ranked

229
citing authors

#	ARTICLE	IF	CITATIONS
1	A novel model on time-resolved photoluminescence measurements of polar InGaN/GaN multi-quantum-well structures. <i>Scientific Reports</i> , 2017, 7, 45082.	3.3	26
2	Low-temperature-dependent property in an avalanche photodiode based on GaN/AlN periodically-stacked structure. <i>Scientific Reports</i> , 2016, 6, 35978.	3.3	11
3	Study on spin and optical polarization in a coupled InGaN/GaN quantum well and quantum dots structure. <i>Scientific Reports</i> , 2016, 6, 35597.	3.3	10
4	Dislocation analysis of InGaN/GaN quantum dots grown by metal organic chemical vapor deposition. <i>Superlattices and Microstructures</i> , 2016, 99, 221-225.	3.1	15
5	Growth of light-emitting devices based on InGaN quantum dots by MOVPE. , 2015, , .		1
6	Growth and characterization of phosphor-free white light-emitting diodes based on InGaN blue quantum wells and green-yellow quantum dots. <i>Superlattices and Microstructures</i> , 2015, 82, 26-32.	3.1	17
7	Metal-organic-vapor phase epitaxy of InGaN quantum dots and their applications in light-emitting diodes. <i>Chinese Physics B</i> , 2015, 24, 067303.	1.4	17
8	Phosphor-Free White Light-Emitting Diodes Based on InGaN Blue Quantum Wells and Green-Yellow Quantum Dots. , 2014, , .		0
9	InGaN quantum dot green light-emitting diodes with negligible blue shift of electroluminescence peak wavelength. <i>Applied Physics Express</i> , 2014, 7, 025203.	2.4	23
10	Green and Red Light-Emitting Diodes Based on Multilayer InGaN/GaN Dots Grown by Growth Interruption Method. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JG13.	1.5	34